Abstracts

Low-power silicon BJT LNA for 1.9 GHz

J.J. Kucera and U. Lott. "Low-power silicon BJT LNA for 1.9 GHz." 1998 Microwave and Guided Wave Letters 8.3 (Mar. 1998 [MGWL]): 136-137.

A two-stage 1.9-GHz monolithic low-noise amplifier (LNA) with a measured noise figure of 2.3 dB and an associated gain of 15 dB was fabricated in a standard silicon bipolar transistor array. It dissipates 5.2 mW from a 3-V supply including the bias circuitry. Input return loss and isolation are -9 and -20 dB, respectively.

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